



PROTON-ELECTROTEX RUSSIA

Electrically isolated base plate
Industrial standard package
Simplified mechanical design, rapid assembly
Pressure contact

Double Thyristor Module For Phase Control MTx-1250-8-D

Mean on-state current				I _{TAV}		1250 A		
Repetitive peak off-state voltage				V _{DRM}		100...800 V		
Repetitive peak reverse voltage				V _{RRM}				
Turn-off time				t _q		160 μs		
V _{DRM} , V _{RRM} , V	100	200	300	400	500	600	700	800
Voltage code	1	2	3	4	5	6	7	8
T _i , °C	-40...+150							

MT3		MT4		MT5	
Dimensions (mm / inches): - Top view: 5 (0,197), 15 (0,59), 60 (2,362), 60 (2,362), 74 (2,913), 25 (0,984), 20 (0,787), 84 (3,307), $\phi 8,5$ (0,335) DIA, 4 apertures, 40 (1,574), 132 (5,196), 150 (5,9), 180 (7,087), 58 (2,283), 77 (3,031). - Side view: 74 (2,913), 25 (0,984), 20 (0,787), 84 (3,307). - Front view: 132 (5,196), 150 (5,9), 180 (7,087), 58 (2,283), 77 (3,031).					
MT/D3		MD/T3		MT/D5	

All dimensions in millimeters (inches)

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{TAV}	Maximum allowable mean on-state current	A	1250 1088	$T_c=71\text{ }^{\circ}\text{C}$; $T_c=85\text{ }^{\circ}\text{C}$; 180° half-sine wave; 50 Hz	
I_{TRMS}	RMS on-state current	A	1963	$T_c=71\text{ }^{\circ}\text{C}$; 180° half-sine wave; 50 Hz	
I_{TSM}	Surge on-state current	kA	42.0 48.0	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=10\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt\geq 1\text{ A}/\mu\text{s}$
			44.0 51.0	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=8.3\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt\geq 1\text{ A}/\mu\text{s}$
I^2t	Safety factor	$\text{A}^2\text{s}\cdot 10^3$	8800 11500	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=10\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt\geq 1\text{ A}/\mu\text{s}$
			8000 10700	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=8.3\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt\geq 1\text{ A}/\mu\text{s}$
BLOCKING					
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	100...800	$T_{j\text{ min}} < T_j < T_{j\text{ max}}$; 180° half-sine wave; 50 Hz; Gate open	
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	200...900	$T_{j\text{ min}} < T_j < T_{j\text{ max}}$; 180° half-sine wave; single pulse; Gate open	
V_D, V_R	Direct off-state and Direct reverse voltages	V	$0.6\cdot V_{DRM}$ $0.6\cdot V_{RRM}$	$T_j=T_{j\text{ max}}$; Gate open	
TRIGGERING					
I_{FGM}	Peak forward gate current	A	8	$T_j=T_{j\text{ max}}$	
V_{RGM}	Peak reverse gate voltage	V	5		
P_G	Gate power dissipation	W	4	$T_j=T_{j\text{ max}}$ for DC gate current	
SWITCHING					
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive ($f=1\text{ Hz}$)	$\text{A}/\mu\text{s}$	1000	$T_j=T_{j\text{ max}}$; $V_D=0.67\cdot V_{DRM}$; $I_{TM}=3200\text{ A}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt\geq 2\text{ A}/\mu\text{s}$	
THERMAL					
T_{stg}	Storage temperature	$^{\circ}\text{C}$	−40...+50		
T_j	Operating junction temperature	$^{\circ}\text{C}$	−40...+150		
$T_{c\text{ op}}$	Operating temperature	$^{\circ}\text{C}$	−40...+125		
MECHANICAL					
a	Acceleration under vibration	m/s^2	50		

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V _{TM}	Peak on-state voltage, max	V	1.40	T _j =25 °C; I _{TM} =3925 A	
V _{T(TO)}	On-state threshold voltage, max	V	0.824	T _j =T _{j max} ;	
r _T	On-state slope resistance, max	mΩ	0.139	0.5 π I _{TAV} < I _T < 1.5 π I _{TAV}	
I _L	Latching current, max	mA	1500	T _j =25 °C; V _D =12 V; Gate pulse: I _G =2 A; t _{GP} =50 μs; di _G /dt≥1 A/μs	
I _H	Holding current, max	mA	300	T _j =25 °C; V _D =12 V; Gate open	
BLOCKING					
I _{DRM} , I _{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	100 4.00	T _j =T _{j max} T _j = 25 °C	V _D =V _{DRM} ; V _R =V _{RRM}
(dv _D /dt) _{crit}	Critical rate of rise of off-state voltage ¹⁾ , min	V/μs	200, 320, 500, 1000, 1600, 2000, 2500	T _j =T _{j max} ; V _D =0.67·V _{DRM} ; Gate open	
TRIGGERING					
V _{GT}	Gate trigger direct voltage, max	V	3.00 2.50 1.50	T _j = T _{j min} T _j =25 °C T _j = T _{j max}	V _D =12 V; I _D =3 A; Direct gate current
I _{GT}	Gate trigger direct current, max	mA	400 250 150	T _j = T _{j min} T _j = 25 °C T _j = T _{j max}	
V _{GD}	Gate non-trigger direct voltage, min	V	0.50	T _j =T _{j max} ; V _D =0.67·V _{DRM} ;	
I _{GD}	Gate non-trigger direct current, min	mA	55.00	Direct gate current	
SWITCHING					
t _{gd}	Delay time, max	μs	0.85	T _j =25 °C; V _D =600 V; I _{TM} =I _{TAV} ; di/dt=200 A/μs;	
t _{gt}	Turn-on time, max	μs	5.00	Gate pulse: I _G =2 A; V _G =20 V; t _{GP} =50 μs; di _G /dt=2 A/μs	
t _q	Turn-off time ²⁾ , max	μs	160	dv _D /dt=50 V/μs; T _j =T _{j max} ; I _{TM} = I _{TAV} ; di _R /dt=-10 A/μs; V _R =100V; V _D =0.67 V _{DRM} ;	
Q _{rr}	Total recovered charge, max	μC	720	T _j =125 °C; I _{TM} =I _{TAV} ;	
t _{rr}	Reverse recovery time, typ	μs	15	di _R /dt=-10 A/μs;	
I _{rr}	Reverse recovery current, max	A	95	V _R =100 V	
THERMAL					
R _{thjc}	Thermal resistance, junction to case			180° half-sine wave, 50 Hz	
	per module	°C/W	0.0250		
	per arm	°C/W	0.0500		
R _{thch}	Thermal resistance, case to heatsink				
	per module	°C/W	0.0080		
	per arm	°C/W	0.0160		
INSULATION					
V _{ISOL}	Insulation test voltage	kV	3.00	Sine wave, 50 Hz; RMS	t=60 sec
			3.60		t=1 sec
MECHANICAL					
M ₁	Mounting torque (M8) ³⁾	Nm	9.00	Tolerance ± 15%	
M ₂	Terminal connection torque (M12) ³⁾	Nm	18.00	Tolerance ± 15%	
m	Weight, max	g	4170		

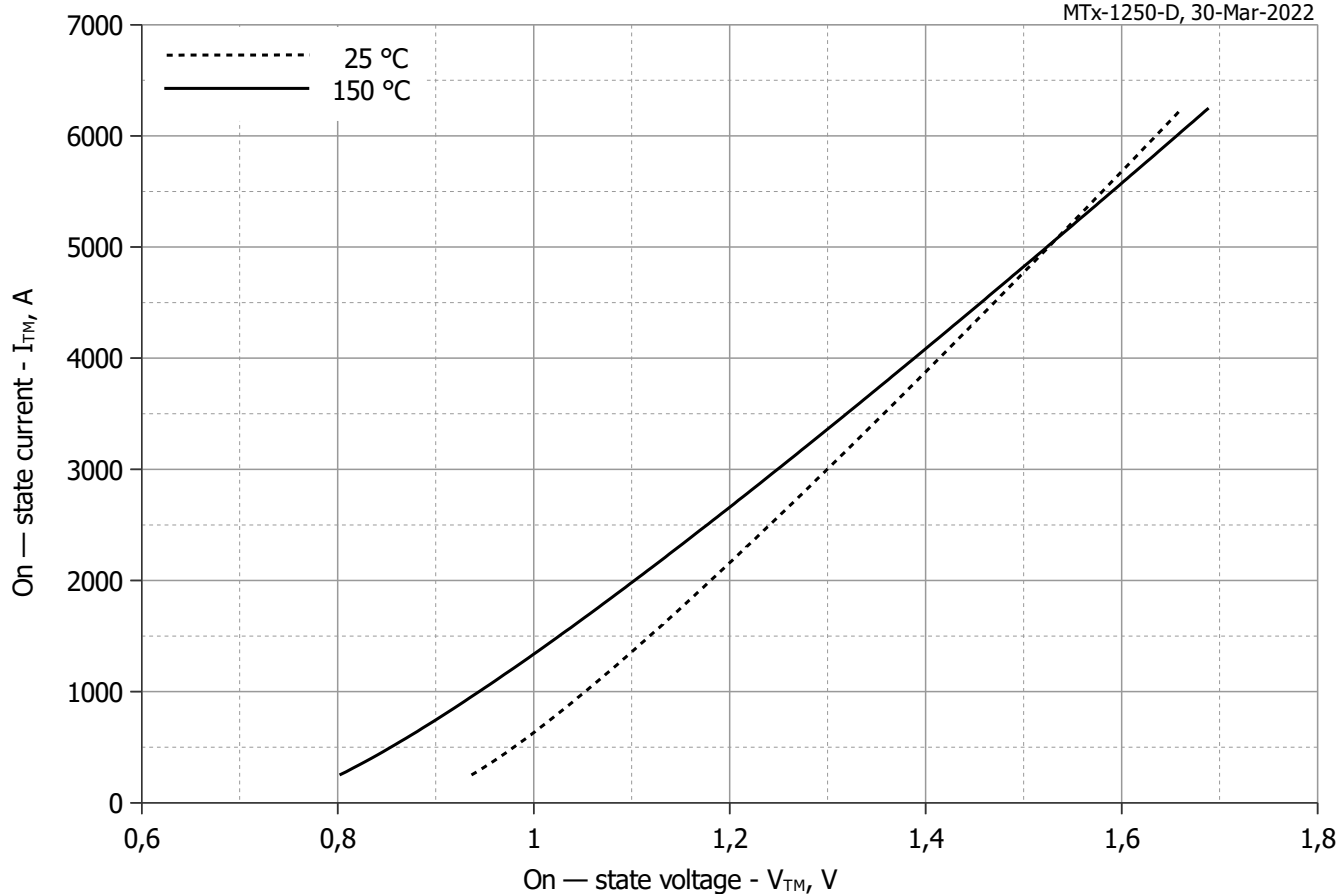


Fig 1 – On-state characteristics of Limit device

Analytical function for On-state characteristic:

$$V_T = A + B \cdot i_T + C \cdot \ln(i_T + 1) + D \cdot \sqrt{i_T}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j\max}$
A	0.84117798	0.72297909
B	0.00009186	0.00010347
C	0.00608911	-0.00288138
D	0.00244737	0.00435555

On-state characteristic model (see Fig. 1)

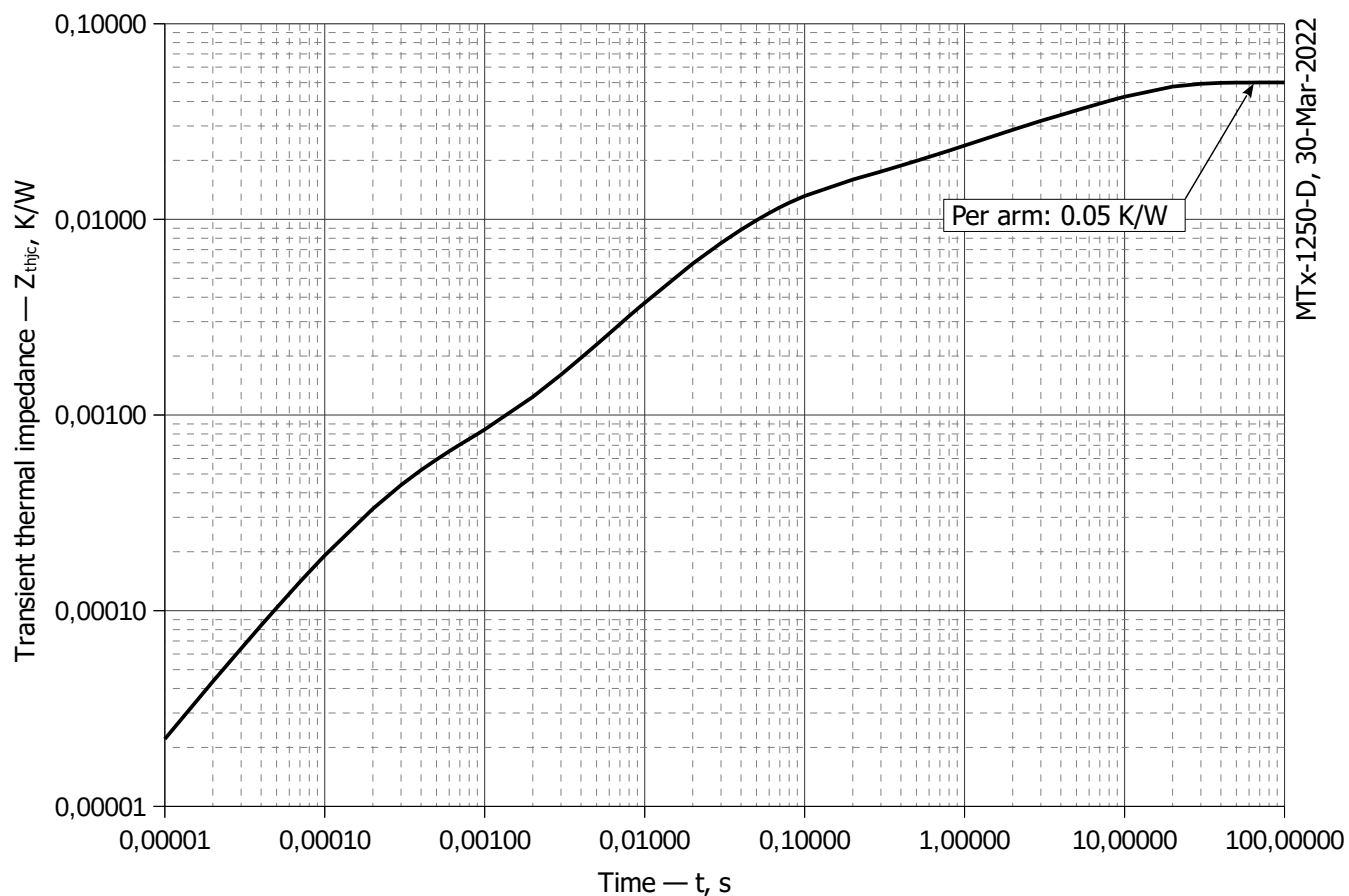


Fig 2 – Transient thermal impedance Z_{thjc} vs. time t

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

i	1	2	3	4	5	6
R_i , K/W	0.02506	0.009643	0.00348	0.009712	0.001719	0.0004399
τ_i , s	8.474	1.11	0.2289	0.04529	0.009524	0.0002414

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

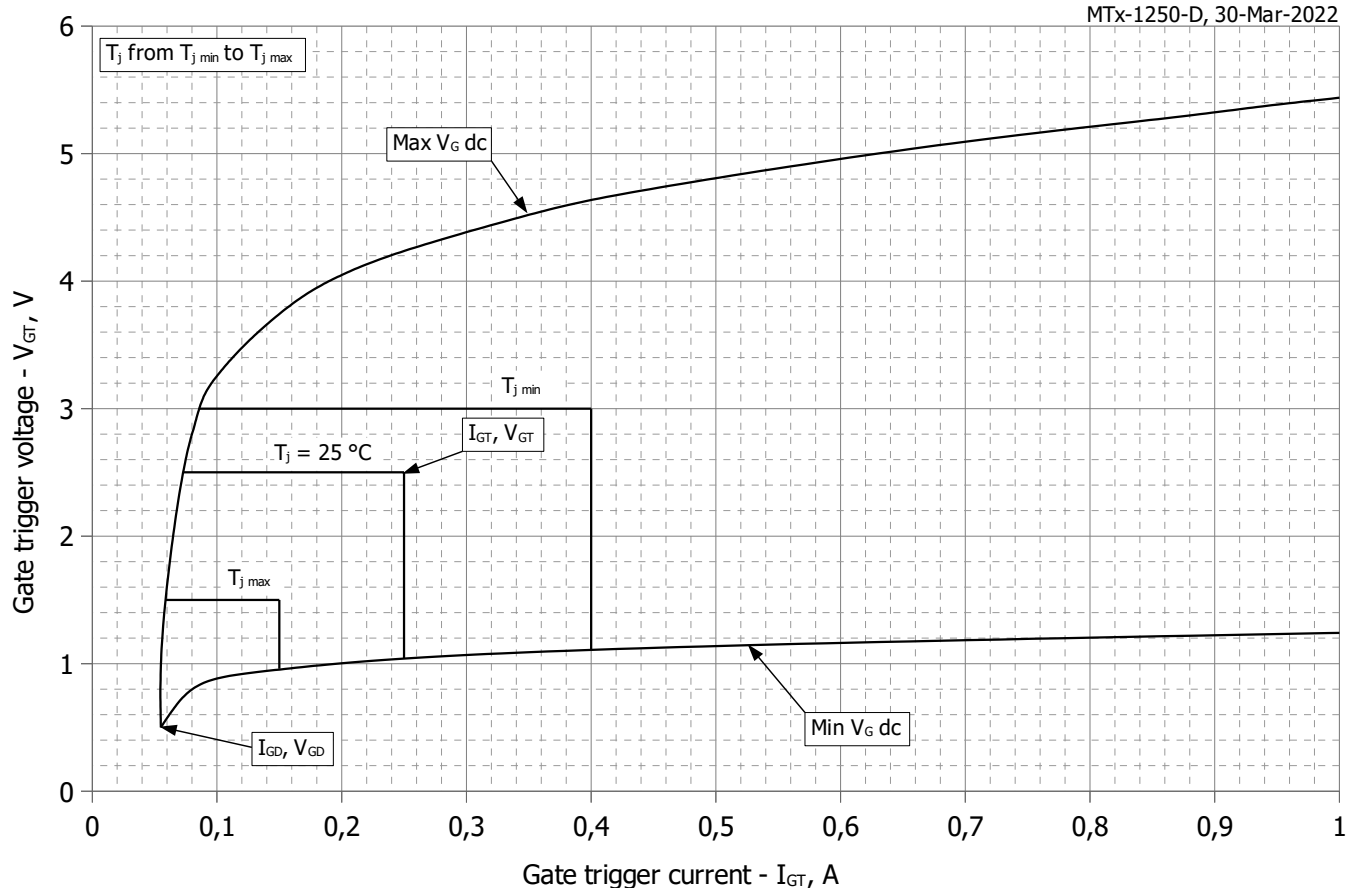


Fig 3 – Gate characteristics – Trigger limits

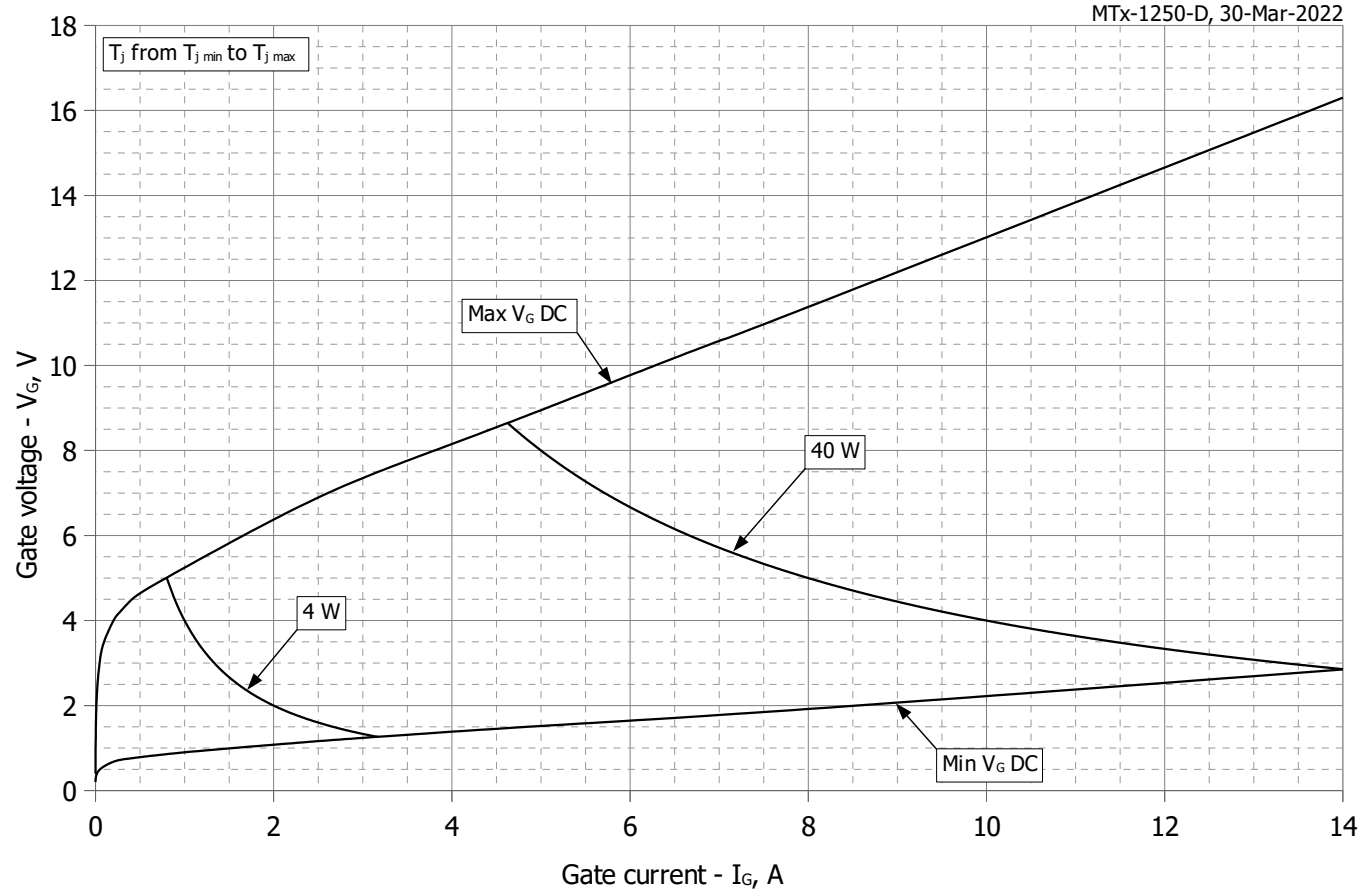


Fig 4 - Gate characteristics – Power curves

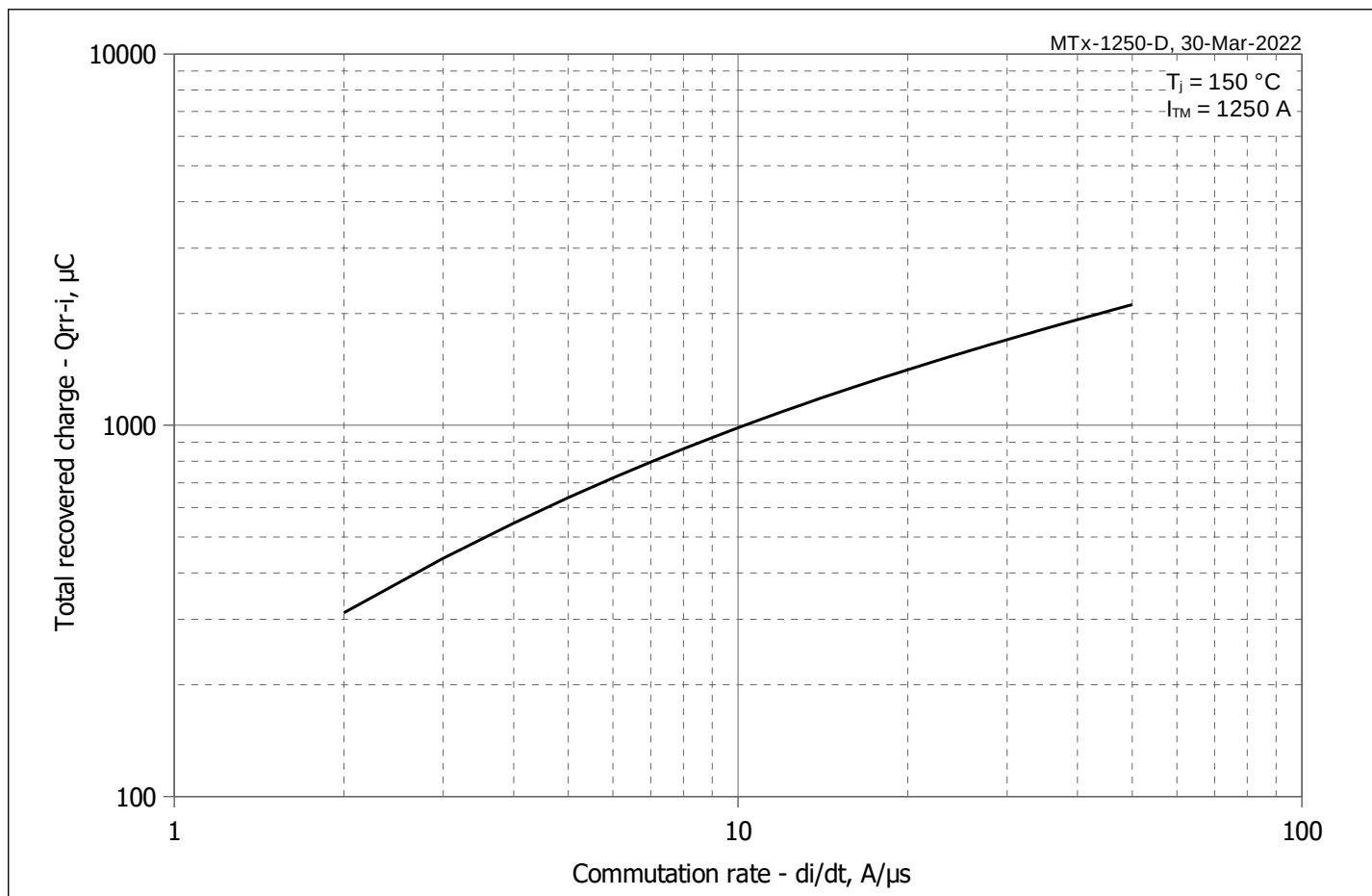


Fig 5 – Maximum recovered charge Q_{rr-i} (integral) vs. commutation rate di_R/dt

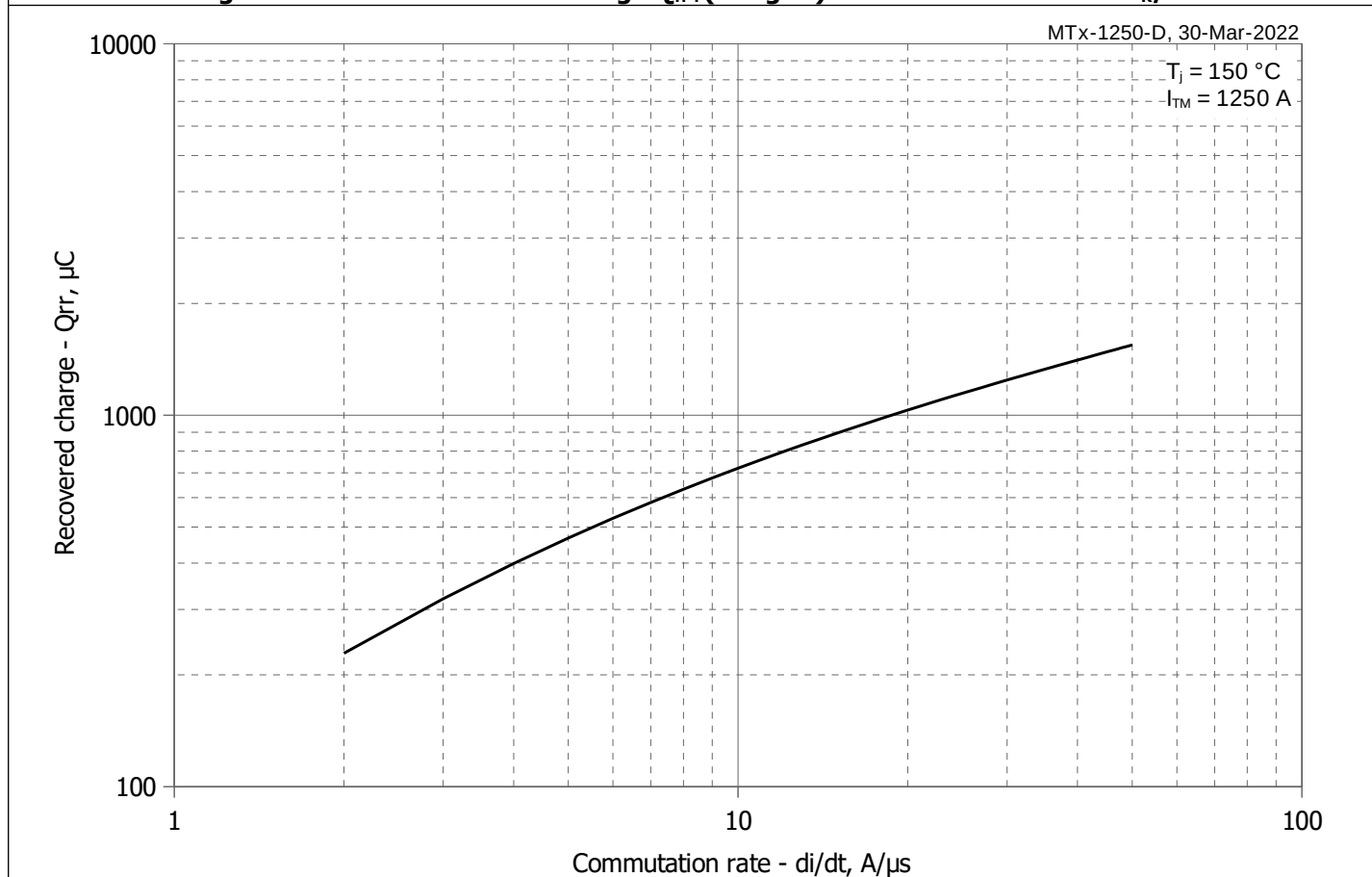


Fig 6 – Maximum recovered charge Q_{rr} vs. commutation rate di_R/dt (25% chord)

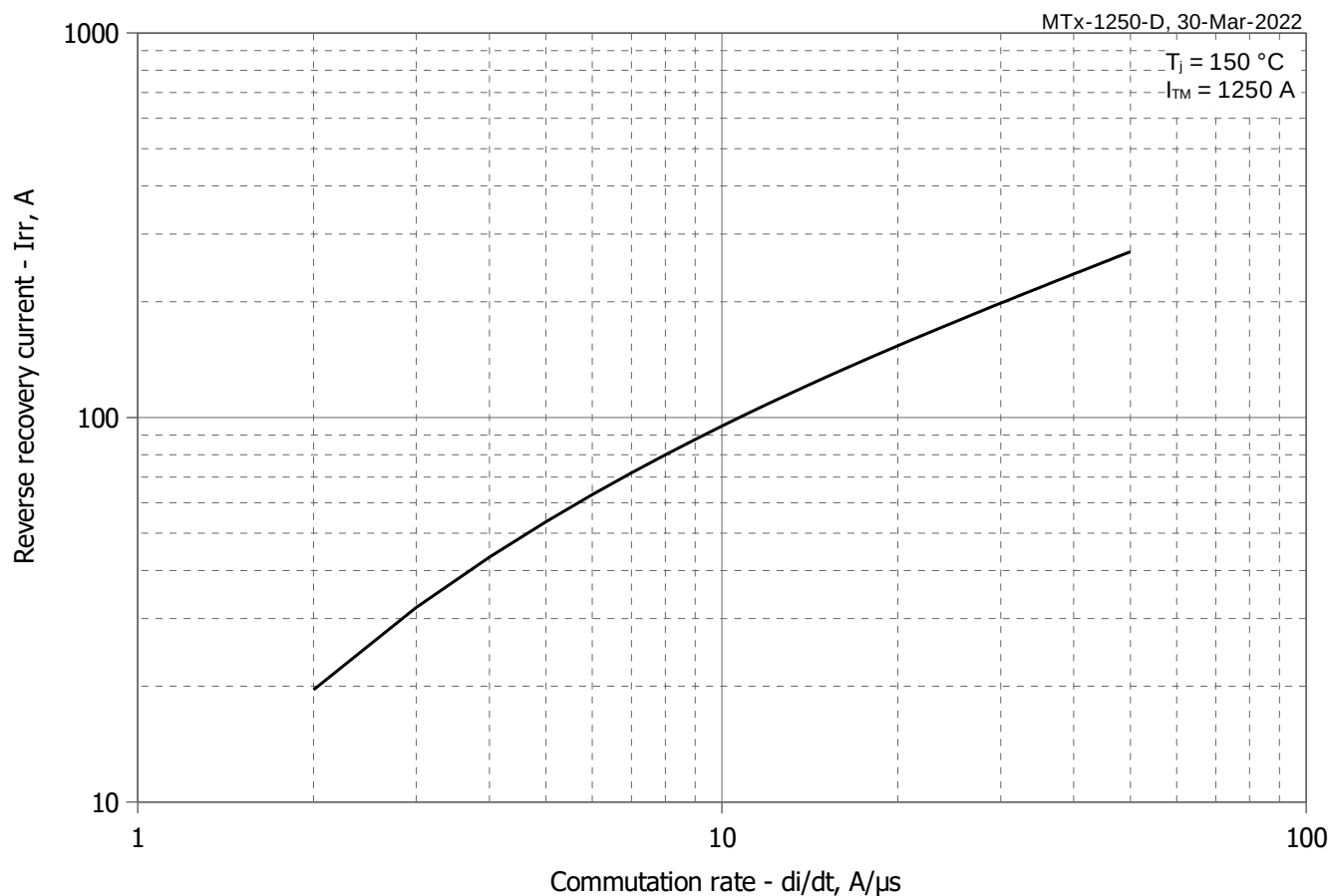


Fig 7 – Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

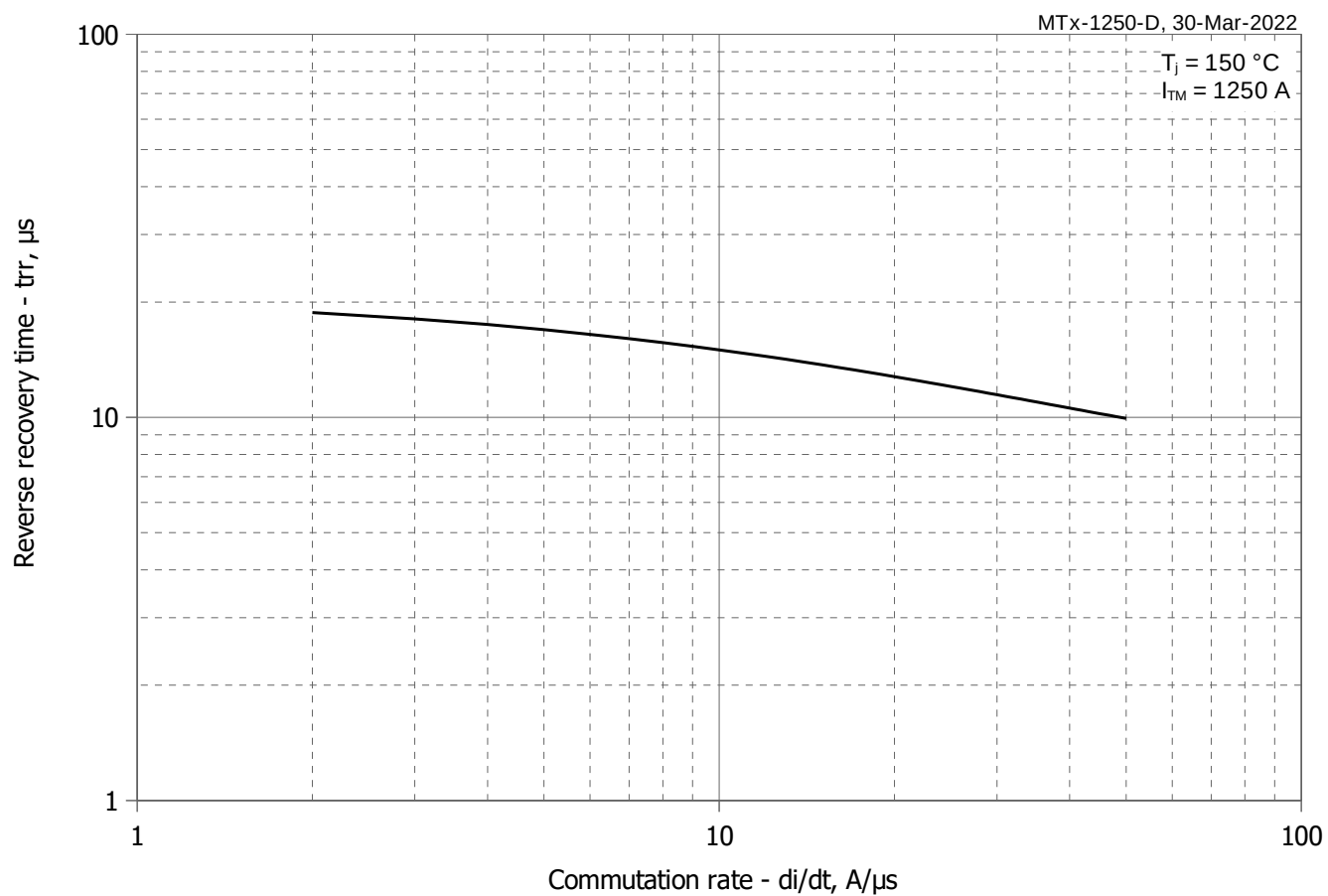


Fig 8 – Maximum recovery time t_{rr} vs. commutation rate di_R/dt (25% chord)

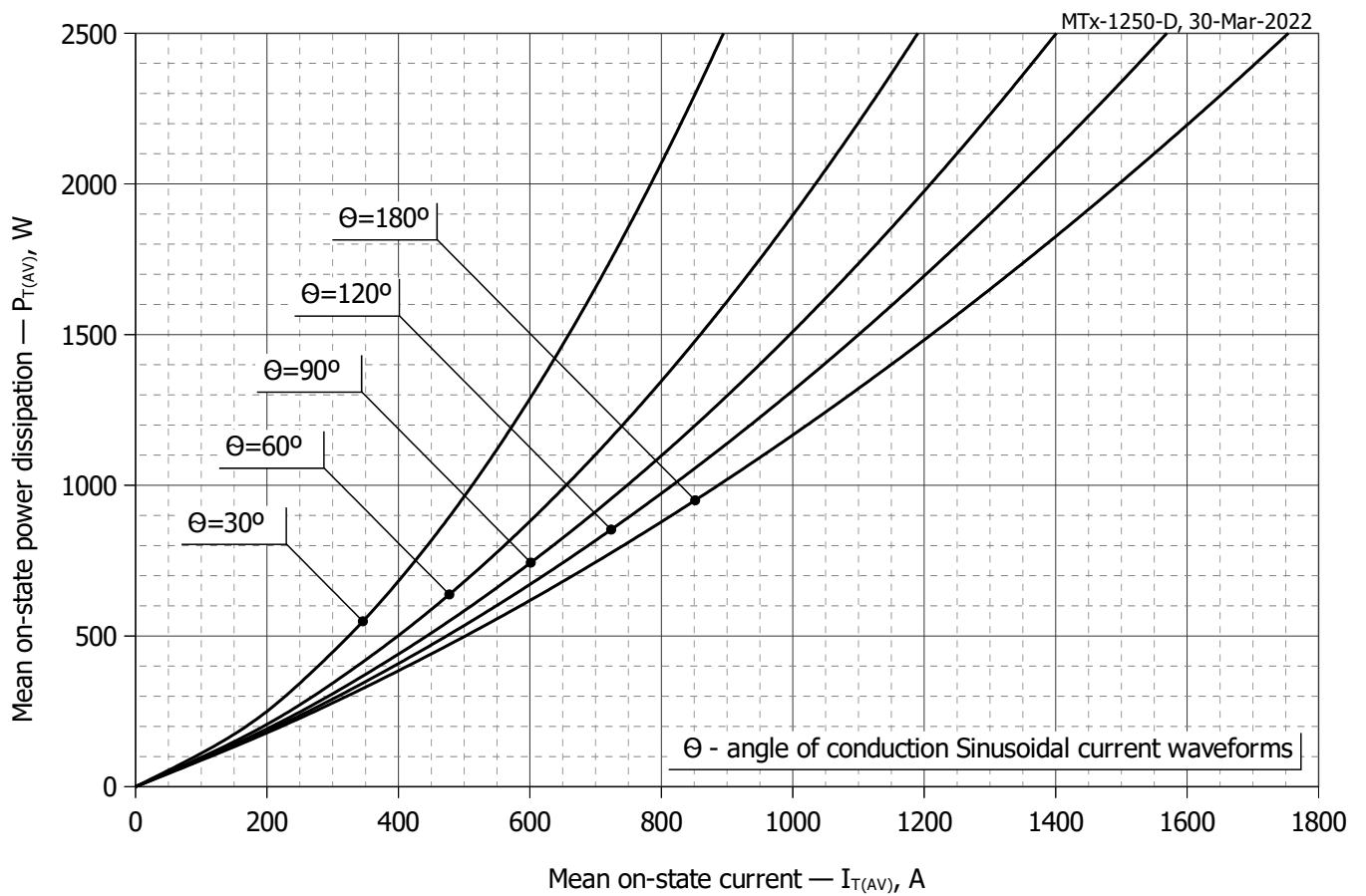


Fig. 9 - Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$)

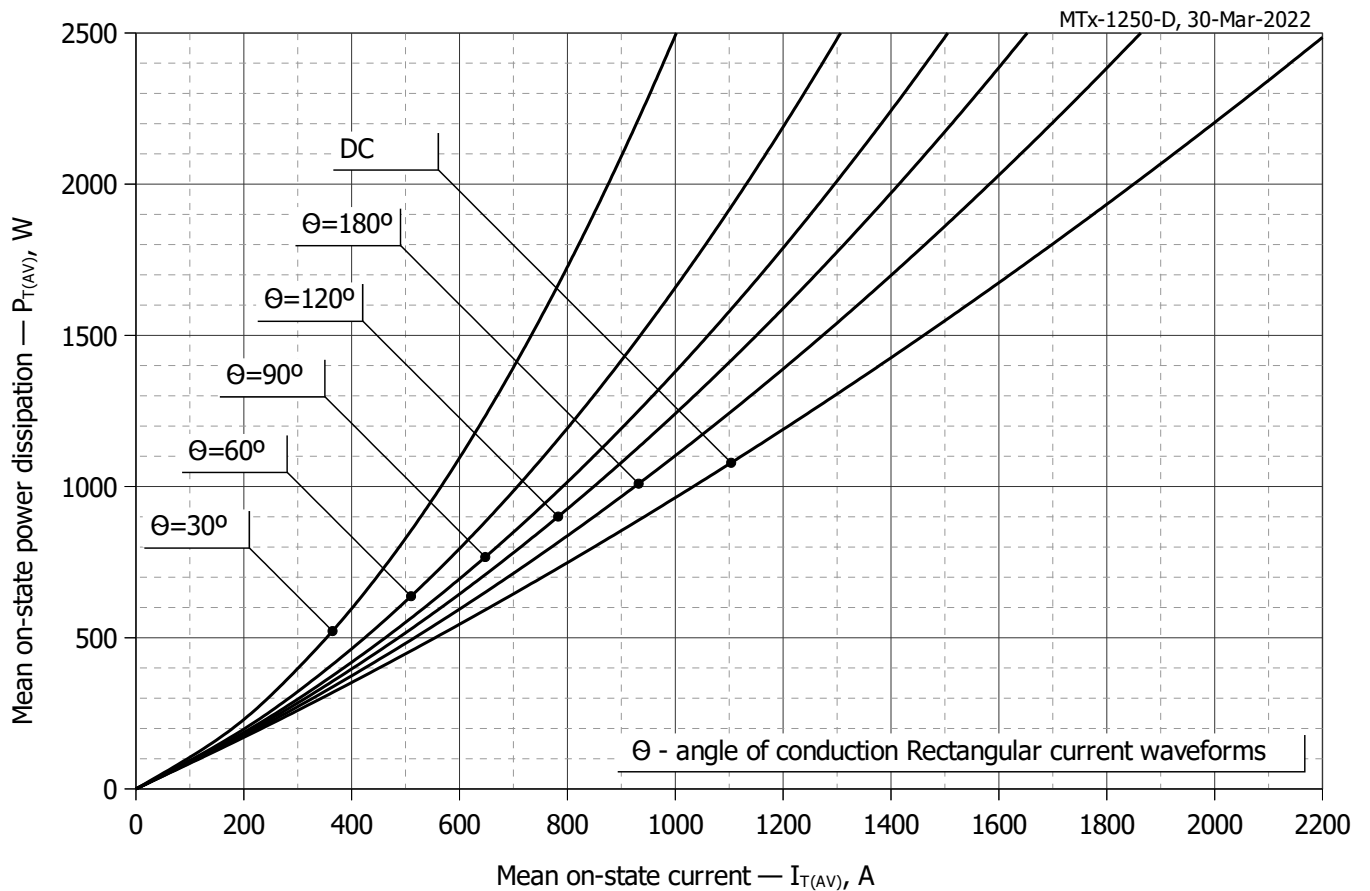


Fig. 10 - Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$)

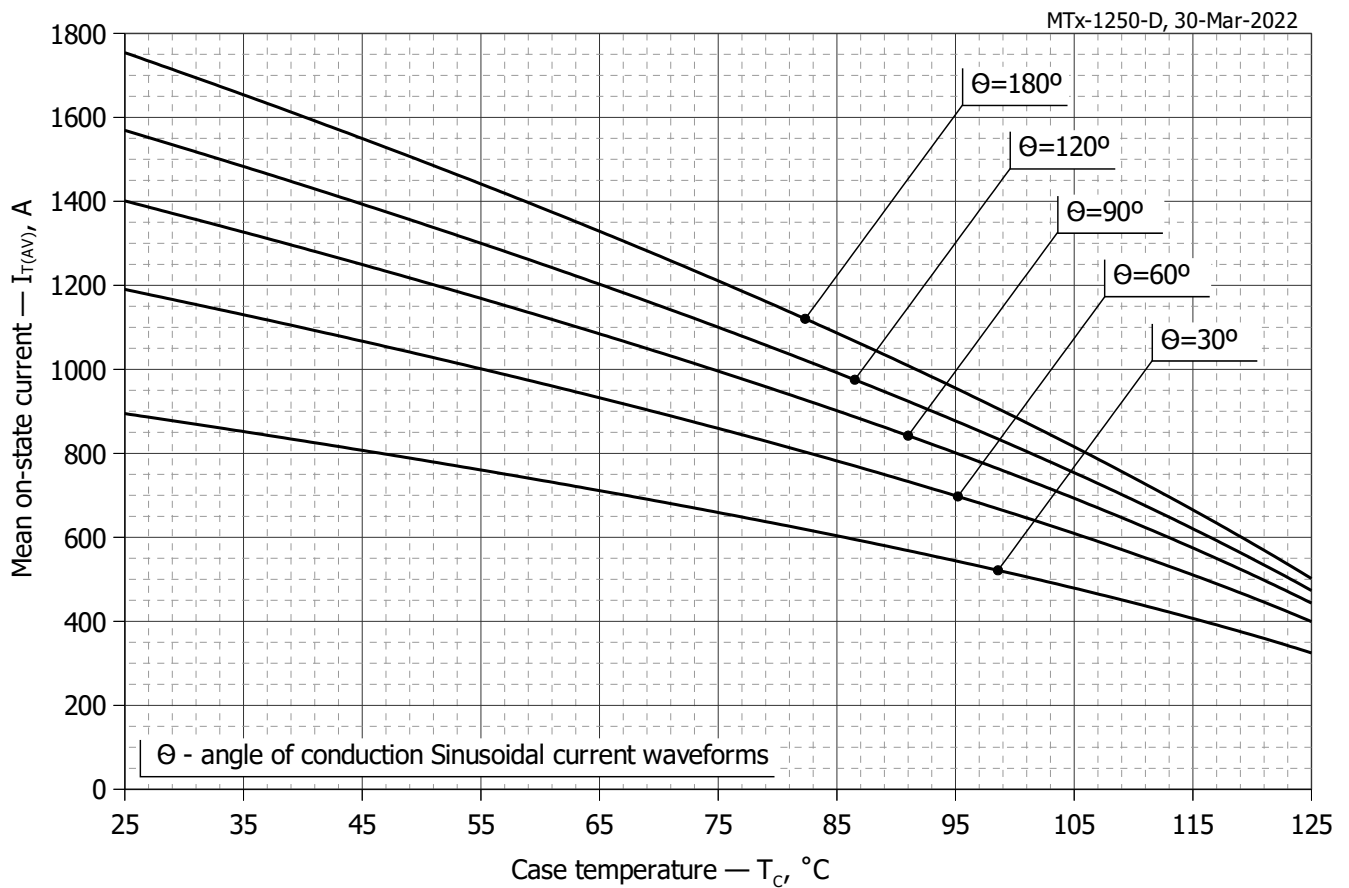


Fig. 11 – Mean on-state current I_{TAV} vs. case temperature T_c for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$)

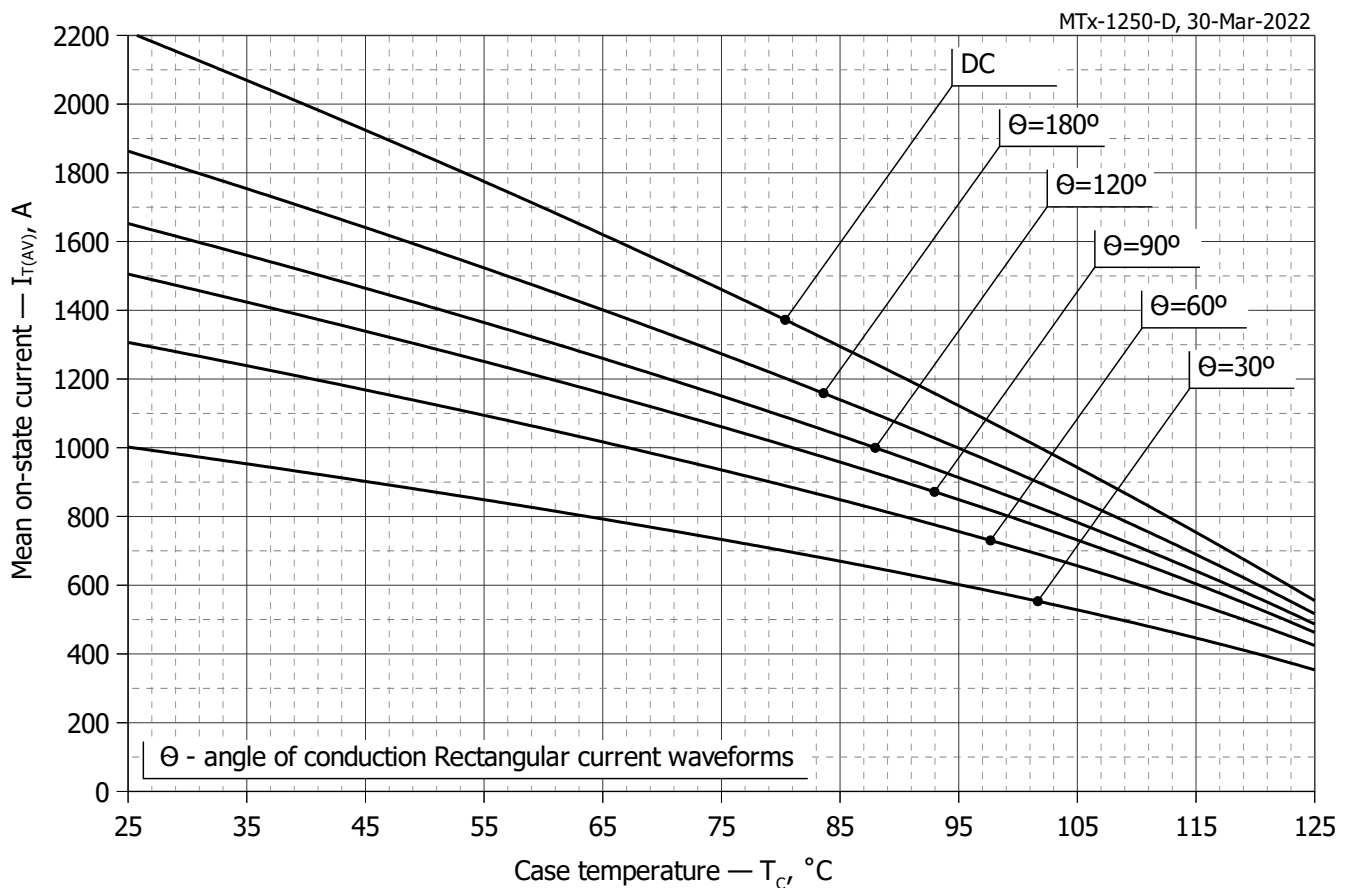


Fig. 12 - Mean on-state current I_{TAV} vs. case temperature T_c for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$)

